

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-10 (Cancelled)

11. (Currently Amended) A method of fabricating a thin film transistor substrate, comprising:

forming a gate electrode on a substrate;

forming a gate pad and a data pad, at least one of the gate pad and the data pad having a pad hole therein;

forming a gate insulation layer on the gate electrode and on the substrate;

forming an active layer on the gate insulation layer;

forming source and drain electrodes on the active layer to form a thin film transistor, the source and drain electrodes being spaced apart from each other and located over the gate electrode, wherein the drain electrode has a first side facing the source electrode and a second side facing said first side;

forming a protection layer on the thin film transistor and on the gate insulation layer, wherein forming the protection layer includes etching the protection layer to cover the first side but not the second side of the drain electrode, and wherein the protection layer includes a contact hole exposing the pad hole; [[and]]

forming a pixel electrode having a plurality of regions wherein a first region is separated from the protection layer at an interval and a second region directly on the gate insulation layer, wherein the second region electrically contacts the second side of the drain electrode, wherein the pixel electrode is formed using a back exposure;

forming a gate pad electrode and a data pad electrode electrically contacting the gate pad and the data pad, respectively, wherein at least one of the gate pad electrode and the data pad electrode is formed using the back exposure light of which passes through the pad hole.

12. (Original) A method of fabricating a thin film transistor substrate according to claim 11, wherein the pixel electrode is formed overlapping the second side.

13. (Original) A method of fabricating a thin film transistor substrate according to claim 11, wherein the pixel electrode is formed of a transparent conductive material.

14. (Original) A method of fabricating a thin film transistor substrate according to claim 13, wherein the transparent conductive material is selected from a group consisting of indium-tin-oxide (ITO) and indium-zinc-oxide (IZO).

15. (Cancelled)

16. (Currently Amended) A method of fabricating a thin film transistor substrate according to claim 11, further including:

forming a gate line on the substrate, wherein the gate line includes the gate pad, and wherein the gate line is formed in electrical contact with the gate electrode;

covering the gate pad with the gate insulation layer and the protection layer;

forming the contact hole through the gate insulation layer and through the protection layer to expose at least part of the gate pad; and

forming ~~the~~ the gate pad electrode that electrically contacts the gate pad through the contact hole.

17. (Previously Presented) A method of fabricating a thin film transistor substrate according to claim 16, wherein the pad hole of the gate pad is formed with a substantially bent shape.

18. (Original) A method of fabricating a thin film transistor substrate according to claim 16, wherein the gate pad electrode is formed on the substrate.

19. (Currently Amended) A method of fabricating a thin film transistor substrate according to claim 11, further including:

forming a data line on the gate insulation layer, wherein the data line includes the data pad, and wherein the data line is formed in electrical contact with the source electrode;

covering the data pad with the protection layer;
forming the contact hole through the protection layer to expose at least part of the data pad; and
forming ~~[[a]]~~ the data pad electrode that electrically contacts the data pad through the contact hole.

20. (Previously Presented) A method of fabricating a thin film transistor substrate according to claim 19, wherein the pad hole of the data pad is formed with a substantially bent shape.

21. (Original) A method of fabricating a thin film transistor substrate according to claim 19, wherein the data pad electrode is formed on the gate insulation layer.

22-33 (Cancelled)